

Name

Speciality

1- We consider a semiconductor of silicon, write the Poisson's equation in each following case and determine (with explanation) if the calculation method to solve the equation is analytical or numerical method

1-1- The semiconductor material is intrinsic including only the free carriers of charge with concentrations n and p such as $n(x) = n_i + 10^{15} \exp\left(-\frac{x}{L_n}\right)$, .. $p(x) = n_i + 10^{15} \exp\left(-\frac{x}{L_p}\right)$

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1-2 The semiconductor material is intrinsic including only the free carriers of charge with concentrations n and p such as $n(x) = n(0) \exp\left(\frac{q\psi(x)}{k_B T}\right)$, $p(x) = p(0) \exp\left(-\frac{q\psi(x)}{k_B T}\right)$

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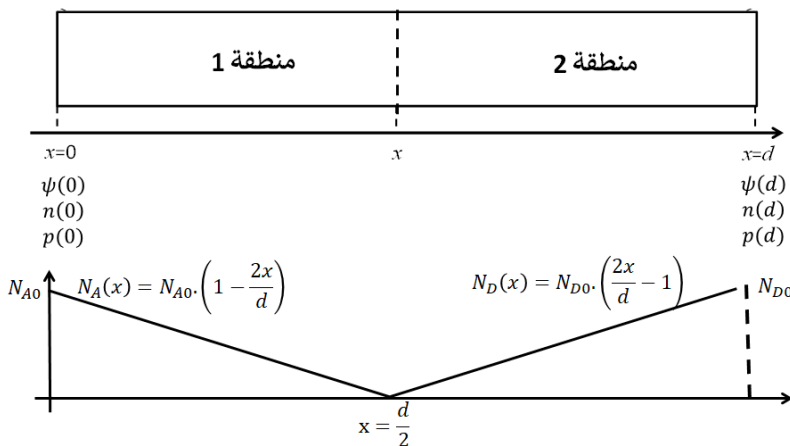
1-3 The semiconductor is doped simultaneously with uniform concentration of N_D donors and N_A acceptors and no free carriers exist

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We consider the following sample -2

$$k_B = 8625 \times 10^{-8} \text{ eV/K}$$

$$h.c \cong 1.2424 \text{ eV} \cdot \mu\text{m}, q = 1.6 \times 10^{-19} \text{ C}$$

$$m_t^* = 0.56 m_0, m_e^* = 1.08 m_0$$

$$N_0 = 2 \cdot \left(\frac{2\pi m_0 k_B T_0}{h^2}\right)^{3/2} = 2.508 \times 10^{19} \text{ cm}^{-3},$$

$$T = T_0 = 300^\circ \text{K}, E_g = 1.12 \text{ eV}$$

The sample is doped with the concentrations

$$N_{A0} = N_{D0} = 10^{17} \text{ cm}^{-3}$$

We consider thermal equilibrium at boundaries

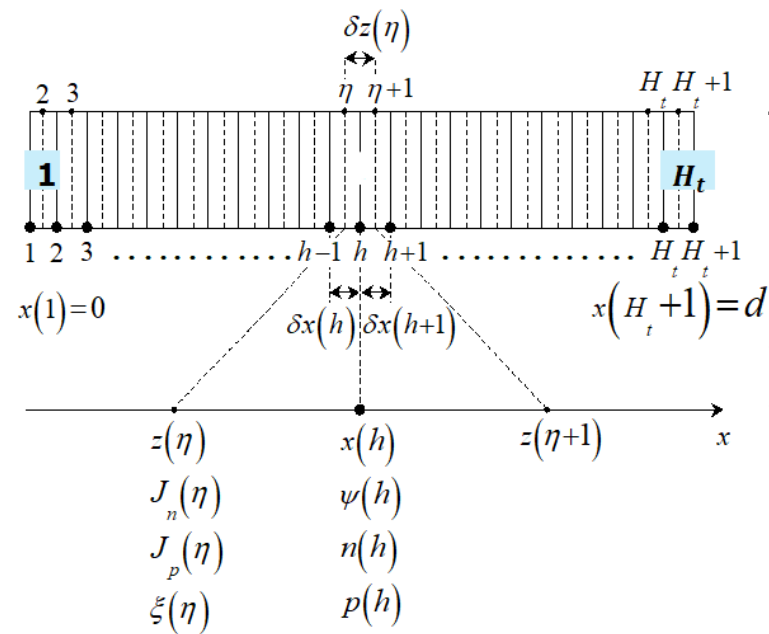
-Write the boundary conditions applied on ψ , n and p , and calculate their values

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3- We consider the spatial discretization shown on the following schema, write the electron continuity equation in continuous formula taking into account only the diffusion current density, we give $g(x) = g_0 = 10^{20} \text{cm}^{-3} \text{s}^{-1}$,

$$U_R(x) = \frac{(n.p - n_i^2)}{(\tau_n(p + n_i) + \tau_p(n + n_i))}$$



4- Write the electron continuity equation in discretised formula and indicate the principal unknowns within it

